

IR Chip--ORT110IRC

1. Scope:

- This specification applies to GaAs/GaAs infrared emitting diode chips.

2. Structure:

- Mesa Type: rough surface.
- Electrodes:
P (Anode) Side: aluminium alloy or gold alloy.
N (Cathode) Side: gold alloy.

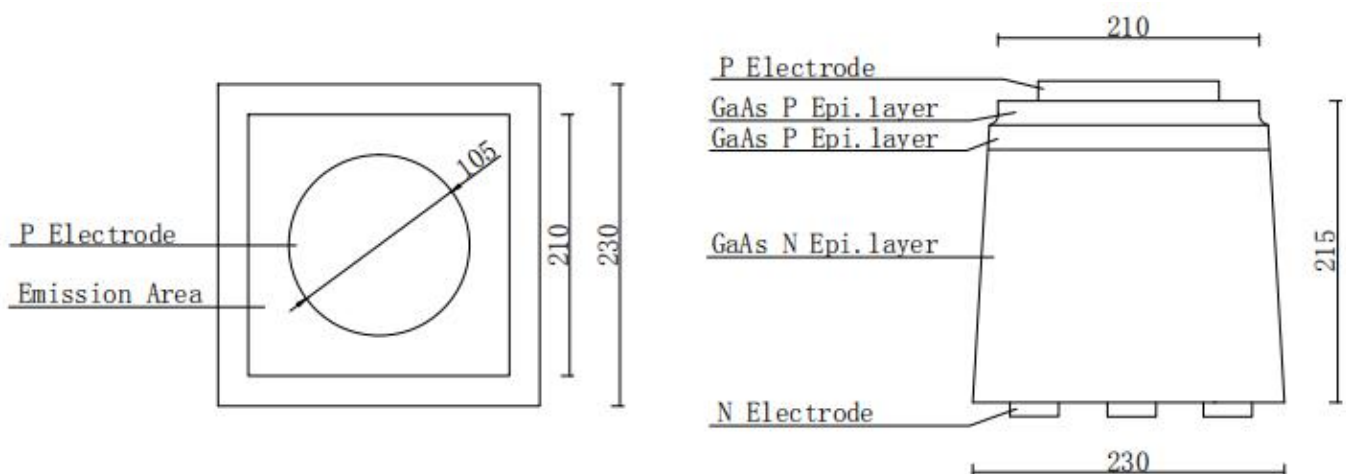
3. Size:

- Top Size: $210\mu\text{m}\times 210\mu\text{m} \pm 30\mu\text{m}$; Bottom Size: $230\mu\text{m}\times 230\mu\text{m} \pm 30\mu\text{m}$
- Chip Height: $215\mu\text{m} \pm 15\mu\text{m}$
- Pad Size: $105\mu\text{m} \pm 10\mu\text{m}$
- Pattern Drawing: fig.1.

4. Electro-Optical Characteristics:

($T_a=+25^\circ\text{C}$)

Parameter	Symbol	Unit	Min	Typ	Max	Test Condition
Forward voltage	V_F	V			1.30	$I_F=20\text{mA}$
Reverse voltage	V_R	V	5			$I_R=10\mu\text{A}$
Peak wavelength	WLP	nm		940		$I_F=20\text{mA}$
Radiated output Power	P_O	mw	0.9			$I_F=20\text{mA}$



unit: μm

fig.1



5. Packing and Labeling:

- Packing: Sheet Type
- Each pellet is mounted on an adhesive sheet with wire-bonded electrode side up.
- Labeling: Each lot has a label sheet、 writing Type、 Lot No、 Pcs、 Avg P_O、 V_F 、 Wlp and quantity of good chips.

6. Application Notes:

- All data are measured by Orient' s tester on bare chips within 98% of the nominal value.
- Measurement error for dominant wavelength and peak wavelength is $\pm 5\text{nm}$